

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

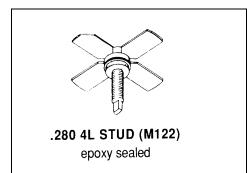
PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1501

RF & MICROWAVE TRANSISTORS UHF TV/LINEAR APPLICATIONS

Features

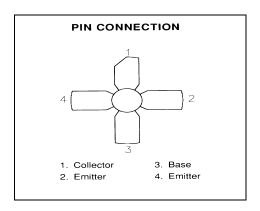
- 860 MHz
- P_{OUT} = 2 WATTS
- $G_P = 8.5 \text{ dB MINIMUM}$
- GOLD METALLIZATION
- CLASS A LINEAR OPERATION
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1501 is a silicon NPN bipolar device specifically designed for high linearity applications in the UHF frequency range including TV Bands IV and V.

Gold metallization and emitter ballasting assure high reliability under Class A linear amplifier operation.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector - Base Voltage	45	V
V _{CEO}	Collector - Emitter Voltage	25	V
V _{EBO}	Emitter - Base Voltage	4	V
Ic	Device Currnet	800	mA
P _{DISS}	Power Dissipation	15.9	W
T _J	Junction Temperature	+200	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Thermal Data

$R_{TH(J-C)}$	Junction-case Thermal Resistance	11.0	°C/W		



MS1501

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value			
		Min.	Typ.	Max.	Unit	
BV _{CBO}	I _C = 10 mA	$I_E = 0 \text{ mA}$	45			V
BV _{CEO}	I _C = 80 mA	$I_B = 0 \text{ mA}$	25			V
BV _{EBO}	I _E = 1 mA	$I_C = 0 \text{ mA}$	4.0			V
I _{CBO}	V _{CB} = 28V	$I_E = 0 \text{ mA}$			0.45	mA
H _{FE}	V _{CE} = 20 V	$I_C = 250 \text{ mA}$	10		100	

DYNAMIC

Symbol	Test Conditions			Value		Unit	
			Min.	Typ.	Max.	Onit	
P _{out}	f = 860 MHz	$V_{CE} = 25V$	$I_C = 450 \text{ mA}$	2			W
G _P	f = 860 MHz	V _{CE} = 25V	I _C = 450 mA	8.5			dB
IMD ₃	P _{SYNC} = 2 W	V _{CE} = 25V	I _C = 450 mA		-60		dBc
Сов	f =1 MHz	V _{CB} = 25V				10	pf

Conditions: $f_1 = 360 \text{ MHz}, f_2 = 863.5 \text{ MHz}, f_3 = 864.5 \text{ MHz}$





PACKAGE MECHANICAL DATA

